

USSN 10/068,159

PATENT RESPONSE

AMENDED SPECIFICATIONS

Please change the "Abstract" as follows:

C Semiconductor devices and stacked die assemblies, ~~and methods of fabricating the~~  
~~devices and assemblies for increasing semiconductor device density are provided,~~ which have at  
least two semiconductor dies disposed on a substrate in a stacked arrangement, the first and  
second dies having first surfaces having bond pads, the second die having a second surface with  
a recessed edge portion along a perimeter of that die, and the recessed edge portion having a  
height sufficient for clearance of bonding elements extending from the first die.

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